
Session Title:	42. Oxide TFT Flexible / Process
Date:	Aug. 25, 2016 (Thursday)
Time:	10:30~12:05
Room	Room B (Halla B)
Session Chairs	Dr. Sung Haeng Cho (ETRI, Korea) Dr. Hendrik Faber (Imperial College London, U.K.)

B42-1

10:30~10:55

[Invited] Oxide Thin Film Transistors for Flexible Devices

Y. Uraoka, J. P. Bermundo, M. Fujii, M. Uenuma, and Y. Ishikawa (NAIST, Japan)

B42-2

10:55~11:20

[Invited] High-Mobility Oxide TFT and its Application in Flexible AMOLED

Lei Wang, Miao Xu, Hua Xu, Min Li, Linfeng Lan, Jianhua Zou, Honglong Ning, Hong Tao, and Junbiao Peng (South China Univ. of Tech., China)

B42-3

11:20~11:35

High Performance Solution-Processed Indium-Free Metal Oxide Thin-Film Transistors

Sooji Nam, Jong-Heon Yang, Sung Haeng Cho, Jihun Choi, and Chi-Sun Hwang (ETRI, Korea)

B42-4

11:35~11:50

Self-Aligned Coplanar a-IGZO TFT Fabricated by UV Irradiation

Myeong-Ho Kim, Sung-Ho Jeon, So-Yang Choi (Hanyang Univ., Korea), Jun-Hyung Lim (Samsung Display Co., Ltd., Korea), and Duck-Kyun Choi (Hanyang Univ., Korea)

B42-5

11:50~12:05

Analysis on PBTS Stability Improvement in Self-Aligned Coplanar InGaZnO Thin Film Transistors

Dohyung Lee, Ju Heyuck Baeck, Taeuk Park, Saeroonter Oh, Jong-Uk Bae, Kwon-Shik Park, and Soo Young Yoon (LG Display Co., Ltd., Korea)